

Switching Diode

BAS16HT1

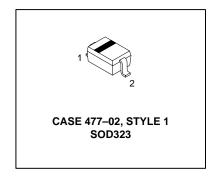
ON Semiconductor Preferred Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	75	Vdc
Peak Forward Current	I _F	200	mAdc
Peak Forward Surge Current	I _{FM(surge)}	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit		
Total Device Dissipation FR-5 Board,* T _A = 25°C Derate above 25°C	P _D	200 1.57	mW mW/°C		
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	°C/W		
Junction and Storage Temperature	T _J , T _{stg}	150	°C		





DEVICE MARKING

BAS16HT1 = A6

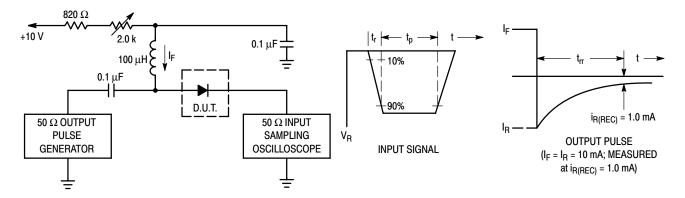
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Reverse Voltage Leakage Current $(V_R = 75 \text{ Vdc})$ $(V_R = 75 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ $(V_R = 25 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	I _R	_ _ _	1.0 50 30	μAdc		
Reverse Breakdown Voltage (I _{BR} = 100 μAdc)	V _(BR)	75	_	Vdc		
Forward Voltage $ \begin{aligned} &(I_F = 1.0 \text{ mAdc}) \\ &(I_F = 10 \text{ mAdc}) \\ &(I_F = 50 \text{ mAdc}) \\ &(I_F = 150 \text{ mAdc}) \end{aligned} $	V _F	_ _ _ _	715 855 1000 1250	mV		
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _D	_	2.0	pF		
Forward Recovery Voltage (I _F = 10 mAdc, t _r = 20 ns)	V _{FR}	_	1.75	Vdc		
Reverse Recovery Time $(I_F = I_R = 10 \text{ mAdc}, R_L = 50 \Omega)$	t _{rr}	_	6.0	ns		
Stored Charge (I _F = 10 mAdc to V_R = 5.0 Vdc, R_L = 500 Ω)	Q _S	_	45	pC		

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

^{*}FR-4 Minimum Pad

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Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA.

- 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.
- 3. t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

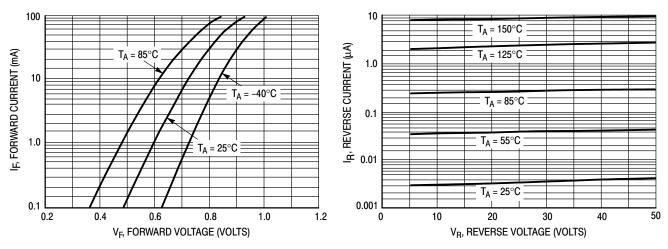


Figure 2. Forward Voltage

Figure 3. Leakage Current

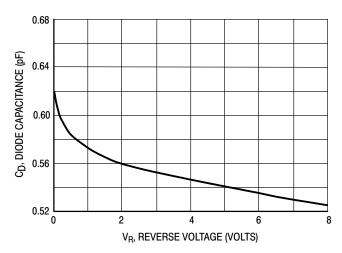
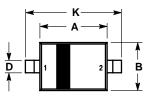


Figure 4. Capacitance

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PACKAGE DIMENSIONS

SOD-323 CASE 477-02 **ISSUE B**





- NOTES:

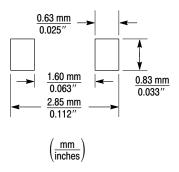
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.60	1.80	0.063	0.071	
В	1.15	1.35	0.045	0.053	
С	0.80	1.00	0.031	0.039	
D	0.25	0.40	0.010	0.016	
Е	0.15 REF		0.006 REF		
Н	0.00	0.10	0.000	0.004	
J	0.089	0.177	0.0035	0.0070	
К	2.30	2 70	0.091	0 106	

STYLE 1: PIN 1. CATHODE 2. ANODE



SOD-323 Soldering Footprint

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